

L Number	Hits	Search Text	DB	Time stamp
1	131402	\$3prom ((non-volatile nonvolatile flash) adj2 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 10:17
8	25292	(\$3prom ((non-volatile nonvolatile flash) adj2 memory)) and (isolation STI BOX LOCOS swami)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 10:18
15	376	(gate electrode) near5 damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 10:19
22	28	(\$3prom ((non-volatile nonvolatile flash) adj2 memory)) and ((gate electrode) near5 damascene)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 14:44
29	8	("5032881"   "5643813"   "5707897"   "5731242"   "5753525"   "5767005"   "6060358"   "6080624").PN.	USPAT	2002/11/14 11:21
37	371	(gate or ((gate control) adj electrode)) near10 interconnect\$3 near20 (simultaneous simultaneously "same time")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 11:40
44	25585	remov\$3 near6 (sacrificial disposable dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 14:48
51	120	((gate electrode) near5 damascene) and (remov\$3 near6 (sacrificial disposable dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 15:57
58	134986	((trench groove opening hole via patterned) near3 (dielectric insulation insulating insulator sacrificial disposable removable))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 16:50
65	55049	((trench groove opening hole via patterned) near3 (metal polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3 deposit\$3 form\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 16:51
72	8456	(((trench groove opening hole via patterned) near3 (dielectric insulation insulating insulator sacrificial disposable removable))) same (((trench groove opening hole via patterned) near3 (metal polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3 deposit\$3 form\$3) )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 16:50
79	5988	(((trench groove opening hole via patterned) near3 (metal polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3 deposit\$3 form\$3) ) near20 (gate (gate adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 16:54
86	12320	(((trench groove opening hole via patterned) near3 (metal polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3 deposit\$3 form\$3) ) near20 (contact\$3 interconnect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 16:56

93	1628	((trench groove opening hole via patterned) near3 (metal polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3 deposit\$3 form\$3) ) near20 (gate (gate adj electrode)) and (((trench groove opening hole via patterned) near3 (metal polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3 deposit\$3 form\$3) ) near20 (contact\$3 interconnect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 16:56
100	1188	((trench groove opening hole via patterned) near3 (metal polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3 deposit\$3 form\$3) ) near20 (gate (gate adj electrode)) same (((trench groove opening hole via patterned) near3 (metal polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3 deposit\$3 form\$3) ) near20 (contact\$3 interconnect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 16:58
107	164	(remov\$3 near6 (sacrificial disposable dielectric)) and (((trench groove opening hole via patterned) near3 (metal polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3 deposit\$3 form\$3) ) near20 (gate (gate adj electrode)) same (((trench groove opening hole via patterned) near3 (metal polysilicon (polycrystalline adj (si silicon)))) near15 (fill\$3 deposit\$3 form\$3) ) near20 (contact\$3 interconnect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 17:17
114	34017	SRAM (static adj2 memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 17:18
121	23	((gate electrode) near5 damascene) and (SRAM (static adj2 memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 17:23
128	464	438/259,589.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 17:24
135	15	438/259,589.ccls. and (damascene or inlaid inlain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/14 17:26